

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-5. (Canceled)

6. (Previously Presented) An active matrix display device comprising:

a first substrate including an organic light-emitting element, in which a light-emitting layer is formed between an anode and a cathode, and

a second substrate including a thin film transistor electrically connected to the organic light-emitting element, the first substrate being bonded to the second substrate, by using anisotropic conductive paste disposed in a position corresponding to the periphery of the thin film transistor,

the organic light-emitting element being located immediately above the thin film transistor.

7. (Previously Presented) The active matrix display device according to claim 6, further comprising a wiring line on the second substrate, wherein the wiring line is connected to the thin film transistor by the anisotropic conductive paste disposed in a position corresponding to the periphery of the thin film transistor.

8. (New) An active matrix device, comprising:

a first substrate including an electro-optical element; and

a second substrate including a thin film transistor electrically connected to the electro-optical element, the first substrate being bonded to the second substrate, by using conductive material disposed in a position corresponding to the periphery of the thin film transistor,

the electro-optical element being located in a position corresponding to the thin film transistor.

9. (New) The active matrix device according to claim 8, wherein the electro-optical element is an organic light-emitting element, in which a light-emitting layer is formed between an anode and a cathode.

10. (New) The active matrix device according to claim 8, wherein the conductive material is an anisotropic conductive paste.

11. (New) The active matrix device according to claim 8, further comprising a wiring line on the second substrate, wherein the wiring line is connected to the thin film transistor by the conductive material disposed in a position corresponding to the periphery of the thin film transistor.